

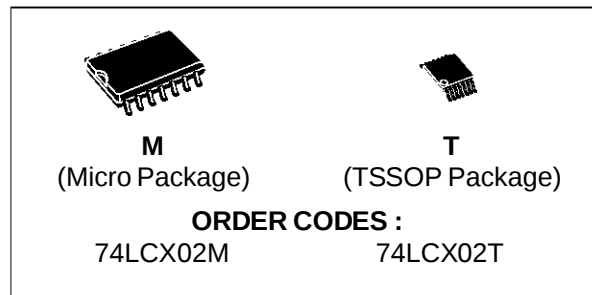
LOW VOLTAGE CMOS QUAD 2-INPUT NOR GATE WITH 5V TOLERANT INPUTS

PRELIMINARY DATA

- 5V TOLERANT INPUTS
- HIGH SPEED:
 $t_{PD} = 5.2 \text{ ns (MAX.) at } V_{CC} = 3V$
- POWER-DOWN PROTECTION ON INPUTS AND OUTPUTS
- SYMMETRICAL OUTPUT IMPEDANCE:
 $|I_{OH}| = I_{OL} = 24 \text{ mA (MIN)}$
- PCI BUS LEVELS GUARANTEED AT 24mA
- BALANCED PROPAGATION DELAYS:
 $t_{PLH} \equiv t_{PHL}$
- OPERATING VOLTAGE RANGE:
 $V_{CC} \text{ (OPR)} = 2.0V \text{ to } 3.6V \text{ (1.5V Data Retention)}$
- PIN AND FUNCTION COMPATIBLE WITH 74 SERIES 02
- LATCH-UP PERFORMANCE EXCEEDS 500mA
- ESD PERFORMANCE:
 $HBM > 2000V$; $MM > 200V$

DESCRIPTION

The LCX02 is a low voltage CMOS QUAD 2-INPUT NOR GATE fabricated with sub-micron silicon gate and double-layer metal wiring C²MOS

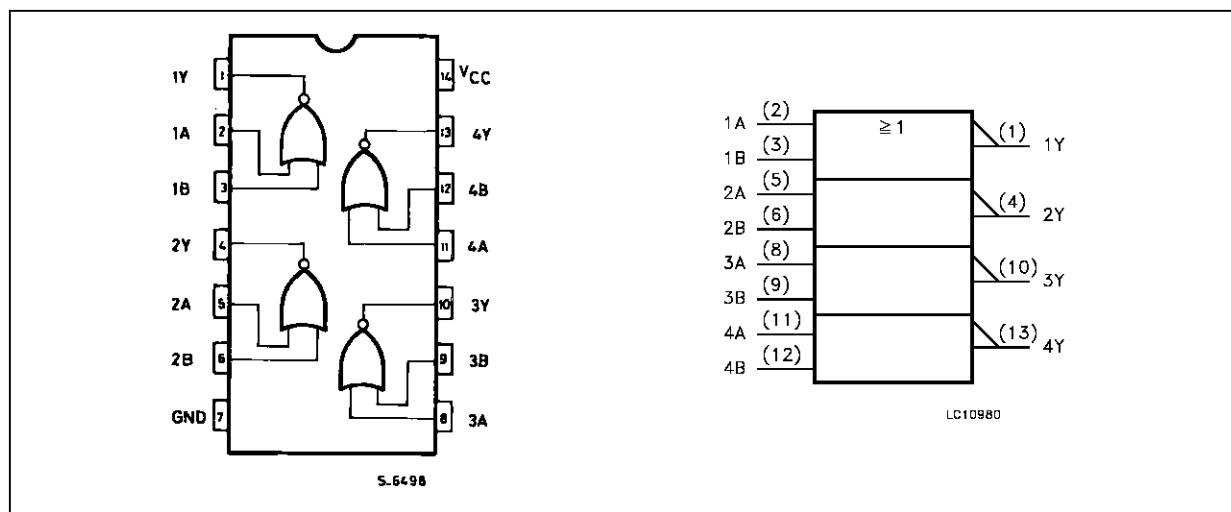


technology. It is ideal for low power and high speed 3.3V applications; it can be interfaced to 5V signal environment for inputs.

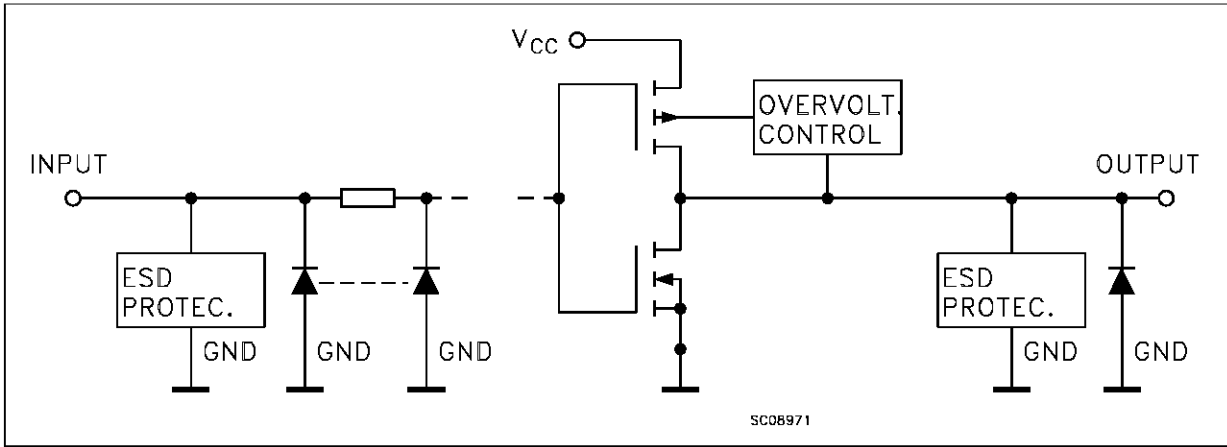
It has same speed performance at 3.3V than 5V, AC/ACT family, combined with a lower power consumption.

All inputs and outputs are equipped with protection circuits against static discharge, giving them 2KV ESD immunity and transient excess voltage.

PIN CONNECTION AND IEC LOGIC SYMBOLS



INPUT AND OUTPUT EQUIVALENT CIRCUIT



PIN DESCRIPTION

PIN No	SYMBOL	NAME AND FUNCTION
2, 5, 8, 11	1A to 4A	Data Inputs
3, 6, 9, 12	1B to 4B	Data Inputs
1, 4, 10, 13	1Y to 4Y	Data Outputs
7	GND	Ground (0V)
14	V _{CC}	Positive Supply Voltage

TRUTH TABLE

A	B	Y
L	L	H
L	H	L
H	L	L
H	H	L

ABSOLUTE MAXIMUM RATINGS

Symbol	Parameter	Value	Unit
V _{CC}	Supply Voltage	-0.5 to + 7.0	V
V _I	DC Input Voltage	-0.5 to + 7.0	V
V _O	DC Output Voltage (V _{CC} =0V)	-0.5 to + 7.0	V
V _O	DC Output Voltage (High or Low State) (note1)	-0.5 to V _{CC} + 0.5	V
I _{IK}	DC Input Diode Current	- 50	mA
I _{OK}	DC Output Diode Current (note2)	± 50	mA
I _O	DC Output Source/Sink Current	± 50	mA
I _{CC}	DC Supply Current per Supply Pin	± 100	mA
I _{GND}	DC Ground Current per Supply Pin	± 100	mA
T _{stg}	Storage Temperature	-65 to +150	°C
T _L	Lead Temperature (10 sec)	300	°C

Absolute Maximum Ratings are those values beyond which damage to the device may occur. Functional operation under these condition is not implied.

1) I_O absolute maximum rating must be observed

2) V_O < GND, V_O > V_{CC}

RECOMMENDED OPERATING CONDITIONS

Symbol	Parameter	Value	Unit
V _{CC}	Supply Voltage (note 1)	2.0 to 3.6	V
V _I	Input Voltage	0 to 5.5	V
V _O	Output Voltage (V _{CC} =0V)	0 to 5.5	V
V _O	Output Voltage (High or Low State)	0 to V _{CC}	V
I _{OH} , I _{OL}	High or Low Level Output Current (V _{CC} = 3.0 to 3.6V)	± 24	mA
I _{OH} , I _{OL}	High or Low Level Output Current (V _{CC} = 2.7 to 3.0V)	± 12	mA
T _{op}	Operating Temperature:	-40 to +85	°C
dt/dv	Input Transition Rise or Fall Rate (V _{CC} = 3.0V) (note 2)	0 to 10	ns/V

1) Truth Table guaranteed: 1.5V to 3.6V

2) V_{IN} from 0.8V to 2.0V

DC SPECIFICATIONS

Symbol	Parameter	Test Conditions		Value		Unit	
		V _{CC} (V)		-40 to 85 °C			
				Min.	Max.		
V _{IH}	High Level Input Voltage	2.7 to 3.6		2.0		V	
V _{IL}	Low Level Input Voltage				0.8	V	
V _{OH}	High Level Output Voltage	2.7 to 3.6	V _I = V _{IH} or V _{IL}	I _O =-100 µA	V _{CC} -0.2	V	
		2.7		I _O =-12 mA	2.2		
		3.0		I _O =-18 mA	2.4		
				I _O =-24 mA	2.2		
V _{OL}	Low Level Output Voltage	2.7 to 3.6	V _I = V _{IH} or V _{IL}	I _O =100 µA		V	
		2.7		I _O =12 mA	0.4		
		3.0		I _O =16 mA	0.4		
		3.0		I _O =24 mA	0.55		
I _I	Input Leakage Current	2.7 to 3.6	V _I = 0 to 5.5 V		±5	µA	
I _{off}	Power Off Leakage Current	0	V _I or V _O = 5.5V		100	µA	
I _{CC}	Quiescent Supply Current	2.7 to 3.6	V _I = V _{CC} or GND		10	µA	
			V _I or V _O = 3.6 to 5.5V		±10		
ΔI _{CC}	ICC incr. per input	2.7 to 3.6	V _{IH} = V _{CC} -0.6V		500	µA	

DYNAMIC SWITCHING CHARACTERISTICS

1) Number of outputs defined as "n". Measured with "n-1" outputs switching from HIGH to LOW or LOW to HIGH. The remaining output is measured in the LOW state.

AC ELECTRICAL CHARACTERISTICS ($C_L = 50 \text{ pF}$, $R_L = 500 \Omega$, Input $t_r = t_f = 2.5 \text{ ns}$)

Symbol	Parameter	Test Condition		Value		Unit
		V _{CC} (V)	Waveform	-40 to 85 °C		
				Min.	Max.	
t _{PLH} t _{PHL}	Propagation Delay Time	2.7 3.0 to 3.6	1	 1.0	6.0 5.2	ns
t _{OSLZ} t _{OSHL}	Output to Output Skew Time (note 1, 2)	3.0 to 3.6			1.0	ns

1) Skew is defined as the absolute value of the difference between the actual propagation delay for any two outputs of the same device switching in the same direction, either HIGH or LOW ($t_{OSLH} = |t_{PLHm} - t_{PLHn}|$, $t_{OSHL} = |t_{PHLm} - t_{PHLn}|$)

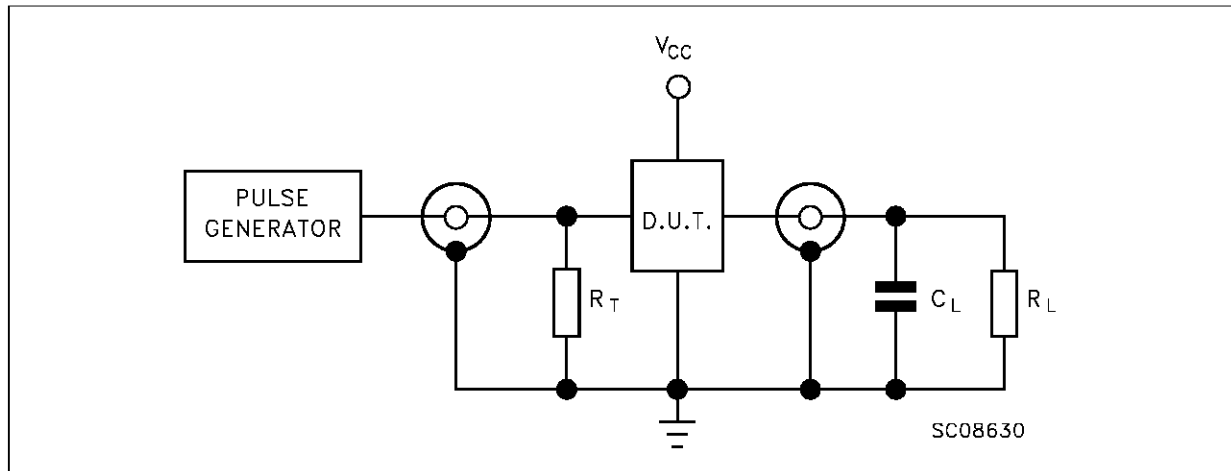
2) Parameter guaranteed by design

CAPACITIVE CHARACTERISTICS

Symbol	Parameter	Test Conditions		Value			Unit
		V _{CC} (V)		T _A = 25 °C			
				Min.	Typ.	Max.	
C _{IN}	Input Capacitance	3.3	V _{IN} = 0 to V _{CC}		6		pF
C _{PD}	Power Dissipation Capacitance (note 1)	3.3	f _{IN} = 10MHz V _{IN} = 0 or V _{CC}		43		pF

1) C_{PD} is defined as the value of the IC's internal equivalent capacitance which is calculated from the operating current consumption without load. Average operating current can be obtained by the following equation. $I_{CC(opr)} = C_{PD} \cdot V_{CC} \cdot f_{IN} + I_{CCD}/n$ (per circuit)

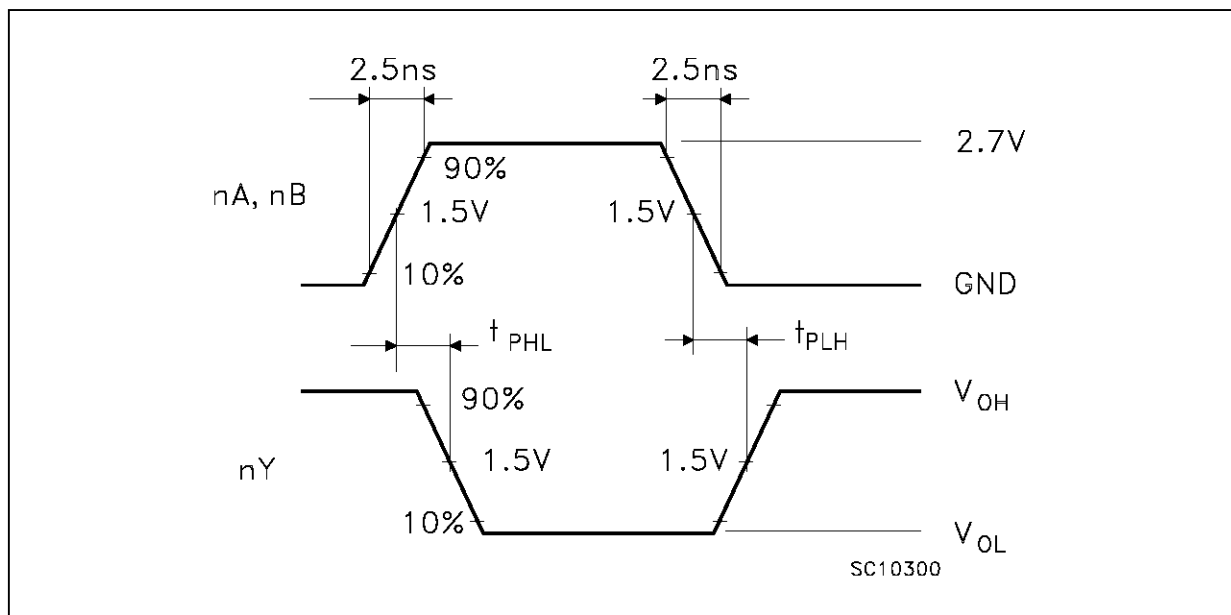
TEST CIRCUIT



C_L = 50 pF or equivalent (includes jig and probe capacitance)

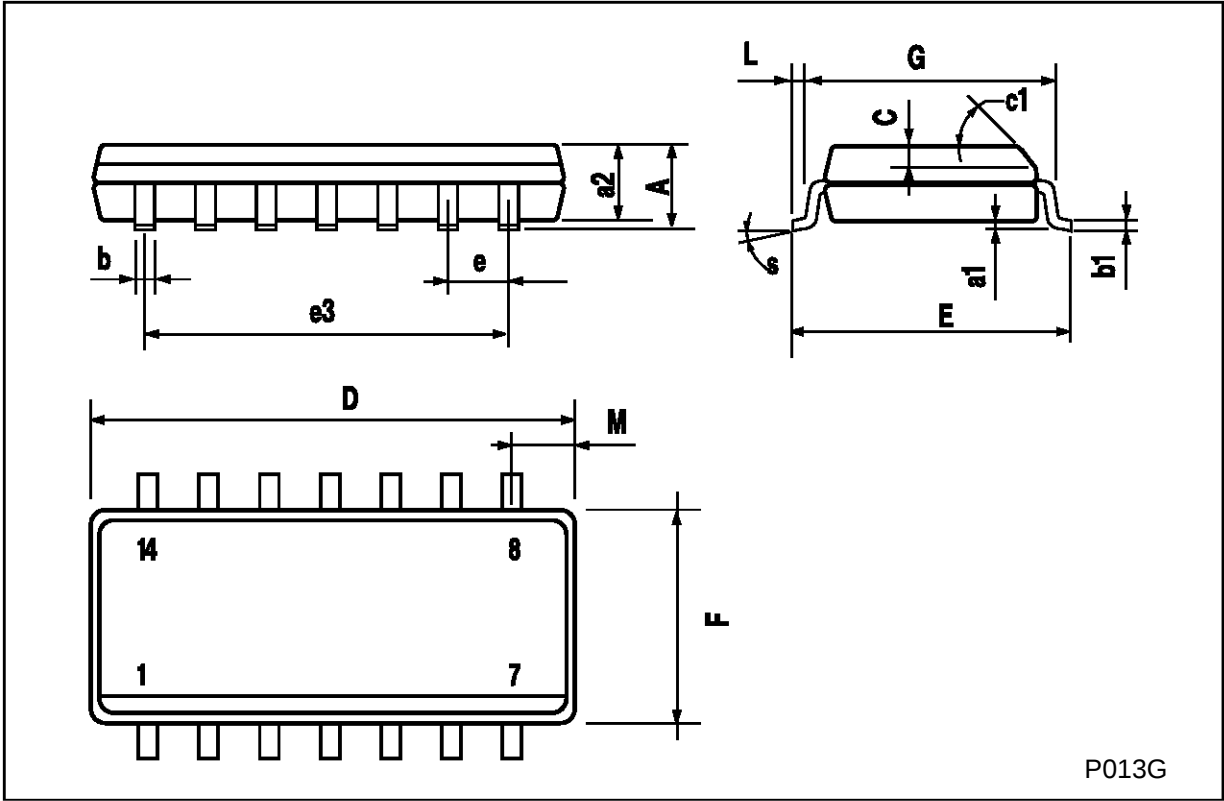
R_L = 500Ω or equivalent

R_T = Z_{out} of pulse generator (typically 50Ω)

WAVEFORM: PROPAGATION DELAYS ($f=1\text{MHz}$; 50% duty cycle)

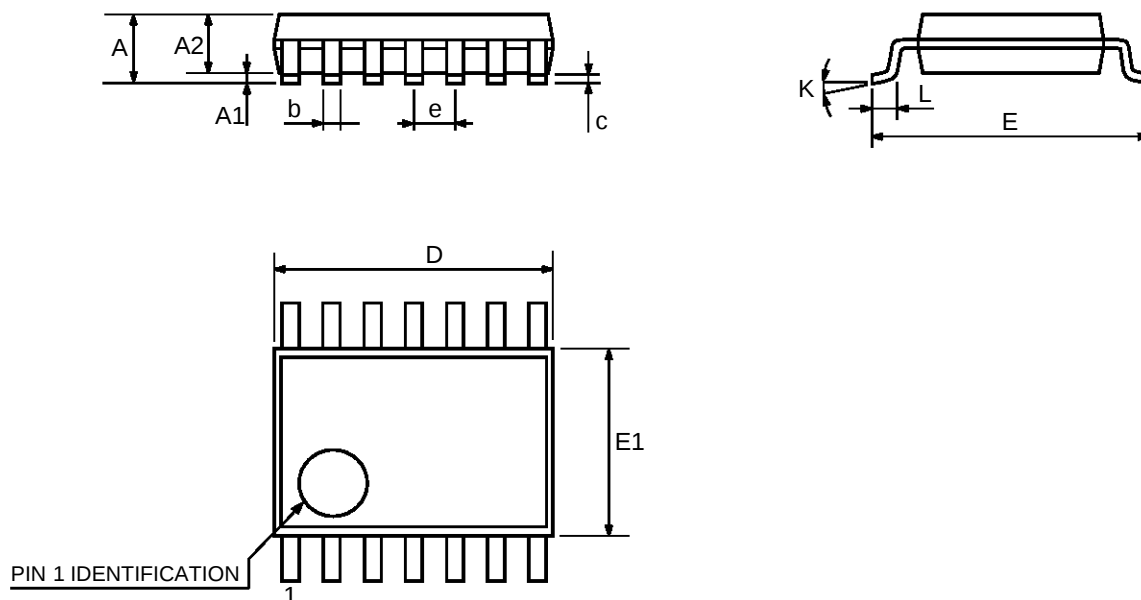
SO14 MECHANICAL DATA

DIM.	mm			inch		
	MIN.	TYP.	MAX.	MIN.	TYP.	MAX.
A			1.75			0.068
a1	0.1		0.2	0.003		0.007
a2			1.65			0.064
b	0.35		0.46	0.013		0.018
b1	0.19		0.25	0.007		0.010
C		0.5			0.019	
c1	45 (typ.)					
D	8.55		8.75	0.336		0.344
E	5.8		6.2	0.228		0.244
e		1.27			0.050	
e3		7.62			0.300	
F	3.8		4.0	0.149		0.157
G	4.6		5.3	0.181		0.208
L	0.5		1.27	0.019		0.050
M			0.68			0.026
S	8 (max.)					



TSSOP14 MECHANICAL DATA

DIM.	mm			inch		
	MIN.	TYP.	MAX.	MIN.	TYP.	MAX.
A			1.1			0.433
A1	0.05	0.10	0.15	0.002	0.004	0.006
A2	0.85	0.9	0.95	0.335	0.354	0.374
b	0.19		0.30	0.0075		0.0118
c	0.09		0.20	0.0035		0.0079
D	4.9	5	5.1	0.193	0.197	0.201
E	6.25	6.4	6.5	0.246	0.252	0.256
E1	4.3	4.4	4.48	0.169	0.173	0.176
e		0.65 BSC			0.0256 BSC	
K	0°	4°	8°	0°	4°	8°
L	0.50	0.60	0.70	0.020	0.024	0.028



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